

SPICE Model Tutorial of the RSLIC18 AC Loop

AN9824
Rev 0.00
October 1998

The AC loop of the RSLIC18 refers to the voice band path which provides full duplex signal communication and impedance synthesis. The circuit operation is described here in as well as the macromodel used to simulate the AC performance of the device. The architecture is the same for all part numbers available in the RSLIC18 family of ringing subscriber line interface circuits.

The information in this document applies to all part numbers of the RSLIC18 family: HC55180, HC55181, HC55182, HC55183 and HC55184.

Architectural Description

The complete AC response of the device is determined by a the dominant AC loop and a low frequency DC loop. The DC loop provides the loop current limit function and contributes to the AC characteristics below 400Hz. The operation of the DC loop will not be discussed in detail, however the effects of this loop are included in the macromodel.

Voltage Feed Current Sense

The AC loop is designed around a voltage feed current sense architecture. The AC loop current is sensed across a pair of low value resistors which are in series with the Tip and Ring amplifier outputs. These sense resistors are placed within the feedback loop of each amplifier, compensating for voltage loss. All internal resistors use ratio relationships providing superb matching, temperature stability and gain accuracies.

The voltage across each resistor is measured using a differential amplifier, referred to as the sense amplifier (SA). The sense amplifier is configured as a dual differential amplifier. The sense connections to the amplifier are "flipped" resulting in addition of metallic signals (AC voice and DC loop current) and cancellation of longitudinal currents.

The output of the sense amplifier drives an inverting amplifier referred to as the transmit amplifier (TA). The gain of the transmit amplifier is set by the external component RS, which sets the synthesized impedance for the device. The output of the transmit amplifier provides the 4-wire output of the device as well as the feedback required for impedance matching. The feedback signal for impedance matching is inverted with respect to the incoming voice signal at the receive input VRX.

The receiver represents a unity gain current summing node. The voice signal at the VRX input and the feedback signal at the VTX output each drive internal resistors. The currents formed by the respective voltages and resistors are summed by a high impedance current summing junction. The sum of the currents are mirrored and drive the inverting terminal of the Tip and Ring amplifiers. The mirrored output of the receiver sources Tip current and sinks Ring current, providing the differential 2-wire output for the device.

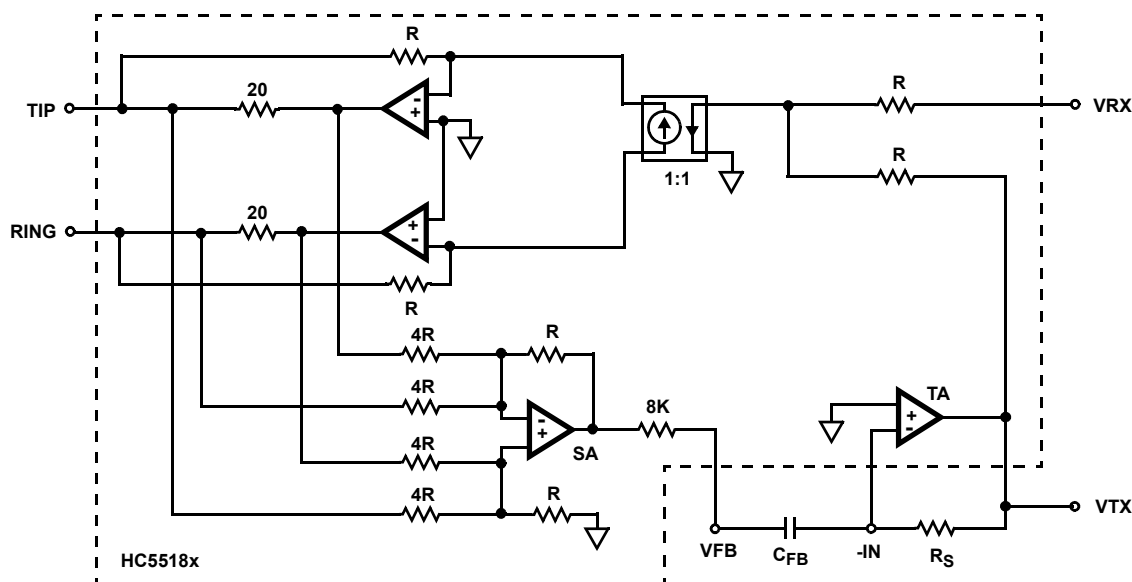


FIGURE 1. RSLIC18 AC SIGNAL TRANSMISSION SIGNAL PATH

Functional Description

The functional blocks of the AC loop are the receiver, tip and ring amplifiers, sense amplifier and transmit amplifier.

Receiver

The receiver provides the current summing node for the voice signals from the CODEC (VRX) and the impedance matching feedback (VTX). The current generated by each voltage signal and internal 200kΩ resistor is summed and mirrored to the Tip and Ring amplifier inverting inputs. Positive voltages at the receive input (VRX) will source current to the Tip amp and sink current from the Ring amp.

Tip and Ring Amplifiers

Both amplifiers are of voltage feedback design with a 200kΩ feedback resistor. The voltage and current relationships of the receiver to Tip and Ring amplifier outputs is shown in Figure 2.

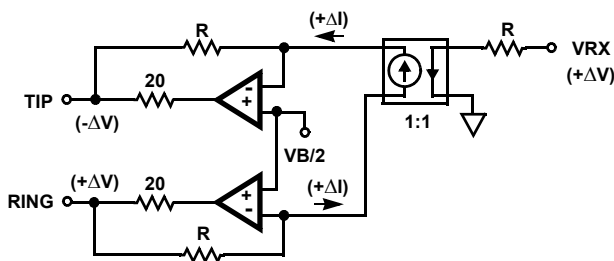


FIGURE 2. RECEIVE INTERFACE

The 20Ω resistors are the sense resistors which provide the loop current information to the sense amplifier. The sense resistor voltage drops are compensated by the feedback loop of each amplifier.

Sense Amplifier

The sense amplifier is configured as a 4 input differential amplifier with a voltage gain of 1/4. The differential input pairs are connected across the internal 20Ω sense resistors. Current flowing out of Tip and into Ring is the convention for positive loop current (I_L) flow. The sense connections across the sense resistors form an inverting relationship between the loop current flow and the output voltage of the sense amp. Figure 3 shows the sense amplifier with connections to the sense resistors.

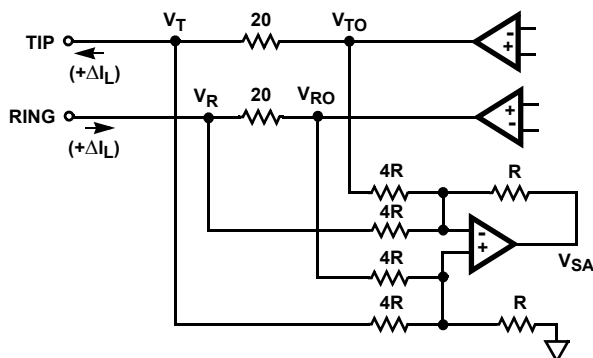


FIGURE 3. SENSE AMPLIFIER SENSING CONNECTIONS

The sense amplifier output voltage as a function of the Tip sense connections can be found by applying superposition to the circuit of Figure 3.

$$V_{SA(T)} = V_T \left(\frac{R \parallel 4R}{4R + R \parallel 4R} \right) \left(1 + \frac{R}{4R} \right) - V_{TO} \left(\frac{R}{4R} \right) \quad (\text{EQ. 1})$$

Simplifying the terms in parenthesis leads to the Tip sense differential relationship of Equation 2.

$$V_{SA(T)} = \frac{1}{4} (V_T - V_{TO}) \quad (\text{EQ. 2})$$

The voltage across the Tip sense resistor is the loop current multiplied by the sense resistor as shown in Equation 3.

$$V_{TO} - V_T = 20I_L \quad (\text{EQ. 3})$$

The voltage at the Tip amplifier output (V_{TO}) is more positive than the Tip sense connection voltage (V_T) as defined by the loop current flow convention of Figure 3. Substituting the loop current term of Equation 3 into the sense amplifier output expression of Equation 2 yields:

$$V_{SA(T)} = \frac{1}{4} (V_T - V_{TO}) = \frac{1}{4} (-20I_L) = -5I_L \quad (\text{EQ. 4})$$

Applying the same superposition analysis to the Ring sense connections results in the complete sense amplifier output expression of Equation 5.

$$V_{SA} = V_{SA(T)} + V_{SA(R)} = (-5I_L) + (-5I_L) = -10I_L \quad (\text{EQ. 5})$$

The final step in defining the sense amplifier functionality is to express the loop current in terms of the load impedance. Since the loop from Tip to Ring represents a closed system the loop current out of Tip equals the loop current into Ring. Therefore the voltage across any impedance in the loop will provide the loop current information. The loop impedance between Tip and Ring (V_T and V_R) is the protection resistors ($2R_P$) and the load impedance (Z_L). Using this voltage and impedance relationship, the sense amplifier output voltage is rewritten as shown in Equation 6. The last term of Equation 6 represent the voltage gain relationship of the sense amp.

$$I_L = \frac{V_T - V_R}{Z_L + 2R_P} \Rightarrow V_{SA} = (V_T - V_R) \frac{-10}{Z_L + 2R_P} \quad (\text{EQ. 6})$$

Transmit Amplifier

The transmit amplifier is a voltage feedback design with the noninverting terminal referenced to ground. It amplifies the sense amplifier output to achieve impedance synthesis. The output equation for the transmit amplifier is provided below.

$$V_{TA} = V_{SA} \left(\frac{-R_S}{8000} \right) = V_{SA} \left(\frac{-400Z_O}{8000} \right) \quad (\text{EQ. 7})$$

The term R_S is the external resistor used to program the synthesized impedance of the device. The value of R_S is equal to $400 \times Z_O$. In addition to impedance matching, the transmit amplifier drives the CODEC transmit interface.

SPICE Macromodel Analysis

The SPICE macromodel represents entire the AC loop of the device. Of the five functional blocks only the receiver is not modeled. The receiver does not contribute significantly to the device bandwidth and is modeled as an ideal current mirror. The four core amplifiers of the design are modeled by two or three pole circuits using voltage controlled voltage sources. Low frequency effects of the loop current limit function are included in the model but will not be discussed in detail. The SPICE net list included at the end of the document should be compatible with any SPICE compatible simulation software.

Model Diagram

The macromodel diagram of Figure 6 is very similar to the functional diagram of Figure 1. The only differences are the addition of the DC loop current limit function and generic blocks representing the amplifiers. The current mirror is modeled using a generic current controlled current source.

AMPLIFIER MODELS

The primary amplifier blocks of the architecture are the tip, ring, sense and transmit amplifiers. Each amplifier will be discussed separately followed by simulation examples using the model.

Tip Amplifier

The Tip amplifier is modeled with a three pole circuit. The open loop gain is 49740 or 94dB and the open loop 3dB bandwidth is 13Hz. An internal compensation capacitor of 5.2pF in parallel with the feedback resistor of 200k Ω forms a zero in the amplifier response at 153kHz. The model for the Tip amplifier

is shown below. The non inverting input is indicated by (+), the inverting input by (-) and the output by (o).

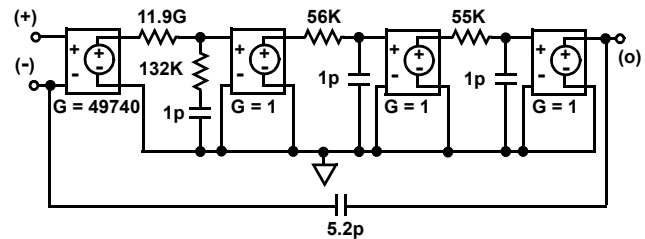


FIGURE 4. TIP AMPLIFIER 3-POLE MODEL

Ring Amplifier

The Ring amplifier is modeled with a three pole circuit. The open loop gain is 59420 or 95dB and the open loop 3dB bandwidth is 12Hz. An internal compensation capacitor of 8pF in parallel with the feedback resistor of 200k Ω forms a zero in the amplifier response at 100kHz. The model for the Ring amplifier is shown below. The non inverting input is indicated by (+), the inverting input by (-) and the output by (o).

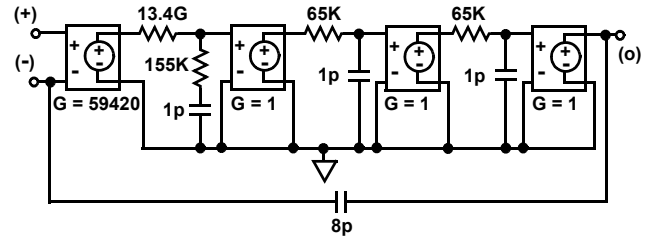


FIGURE 5. RING AMPLIFIER 3-POLE MODEL

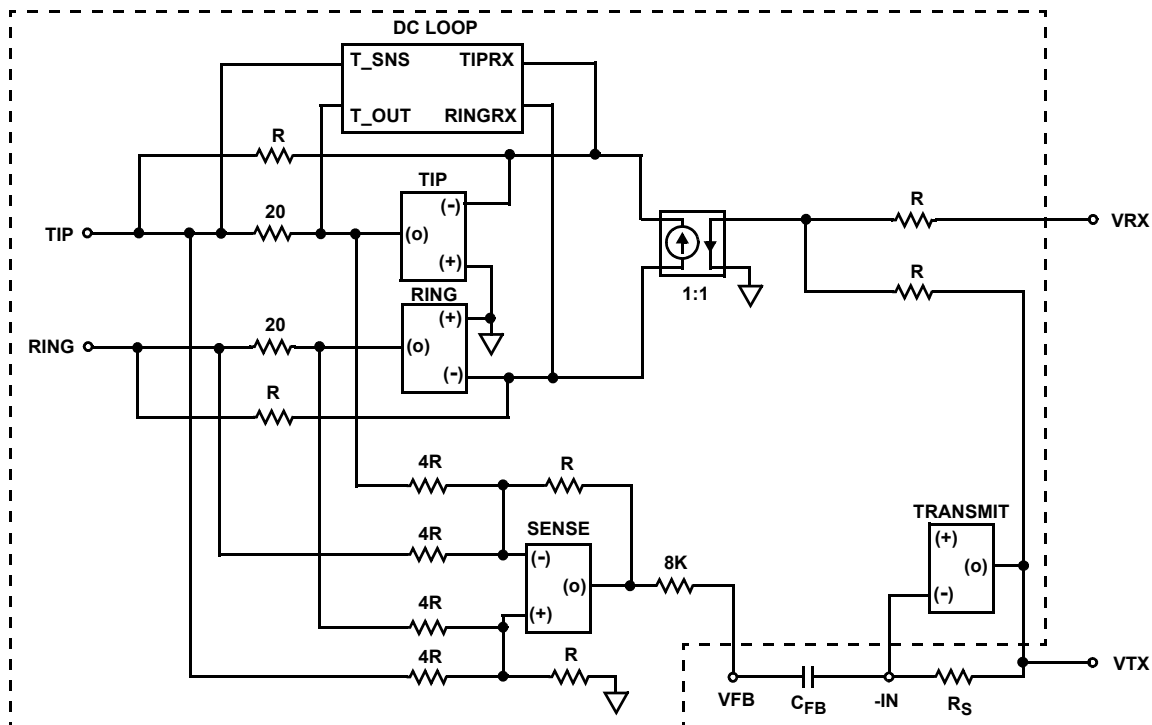


FIGURE 6. AC LOOP MACROMODEL DIAGRAM

Sense Amplifier

The Sense amplifier is modeled with a two pole circuit. The open loop gain is 4716 or 73dB and the open loop 3dB bandwidth is 260Hz. The model for the Sense amplifier is shown below. The non inverting input is indicated by (+), the inverting input by (-) and the output by (o).

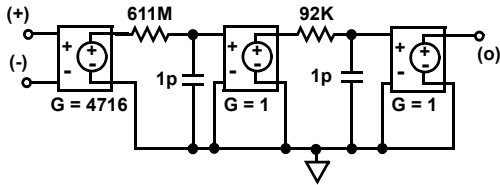


FIGURE 7. SENSE AMPLIFIER 2-POLE MODEL

Transmit Amplifier

The Transmit amplifier is modeled with a two pole circuit. The open loop gain is 4151 or 72dB and the open loop 3dB bandwidth is 127Hz. The model for the Transmit amplifier is shown below. The non inverting input is indicated by (+), the inverting input by (-) and the output by (o).

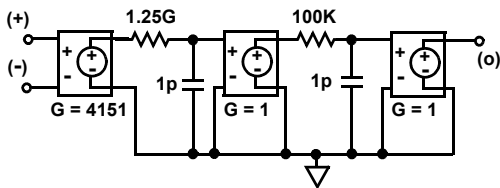


FIGURE 8. TRANSMIT AMPLIFIER 2-POLE MODEL

The gains and component values used in the models were matched to the actual device level simulations of each amplifier. Lab measurements may vary due to component tolerances and process variations.

Simulation Example - Resistive Load

Resistive matching is a misnomer, since the impedance being matched is in the voice band. However, resistive matching is the case when the device synthesizes an impedance to match a purely resistive load. This example will match the device to a 600Ω load impedance, which is the reference impedance for most North American telephony AC transmission specifications.

Device Impedance Synthesis

The device synthesized impedance (Z_O) is defined as the difference between the load impedance (Z_L) and the sum of the protection resistance (R_P).

$$Z_O = Z_L - 2R_P = 600\Omega - 2(35\Omega) = 530\Omega \quad (\text{EQ. 8})$$

Typically the load impedance represents a combination of loop length and phone impedance, therefore a separate term for the loop length (ohms/foot) is not required.

The external resistor, R_S , which programs the synthesized impedance is calculated from the equation shown below.

$$R_S = 400 \times Z_O = 400 \times 530\Omega = 212k\Omega \quad (\text{EQ. 9})$$

The resistor value used in the application circuit will be the standard component value nearest to the calculated value.

G₄₂ Simulation

The G₄₂ frequency response of the device is simulated using the circuit of Figure 9.

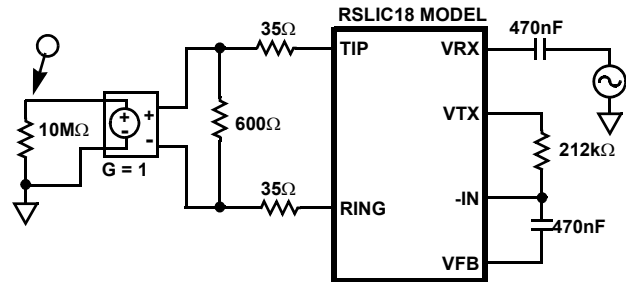


FIGURE 9. G₄₂ RESISTIVE LOAD SIMULATION CIRCUIT

The VRX input of the model is driven by an AC voltage source. The differential voltage across the 600Ω load is converted to single ended by the voltage controlled voltage source with a gain of 1. A dB voltage probe was used to measure the magnitude and a phase voltage probe was used to measure the phase of the frequency response.

EXPECTED RESULTS

The G₄₂ results are predicted using the voltage divider relationship shown below.

$$G_{42} = \frac{-2Z_L}{Z_L + 2R_P + Z_O} = \frac{-2(600)}{600 + 2(35) + 530} = -1 \quad (\text{EQ. 10})$$

The magnitude of the frequency response in the voice band, 300Hz to 3400Hz, should be approximately 0dB and the phase should be nearly 180 degrees.

G₂₄ Simulation

The G₂₄ frequency response of the device is simulated using the circuit of Figure 10.

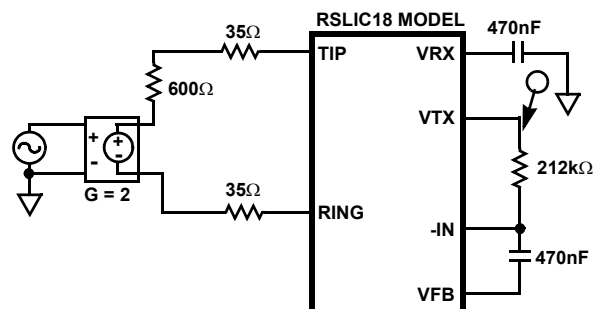


FIGURE 10. G₂₄ RESISTIVE LOAD SIMULATION CIRCUIT

The voltage controlled voltage source converts the single ended AC voltage source to a differential driver for the 2-wire interface. The 4-wire output voltage is measured at the transmit output, VTX, of the device. A dB voltage probe was used to measure the magnitude and a phase voltage probe was used to measure the phase of the frequency response.

EXPECTED RESULTS

The G_{24} results are predicted using the voltage divider relationship shown below.

$$G_{24} = \frac{-Z_O}{Z_L + 2R_P + Z_O} = \frac{-530}{600 + 2(35) + 530} = -0.441 \quad (\text{EQ. 11})$$

The magnitude of the frequency response in the voice band, 300Hz to 3400Hz, should be approximately -7.1dB and the phase should be nearly 180 degrees.

G₄₄ Simulation

The G_{44} frequency response of the device is simulated using the circuit of Figure 11.

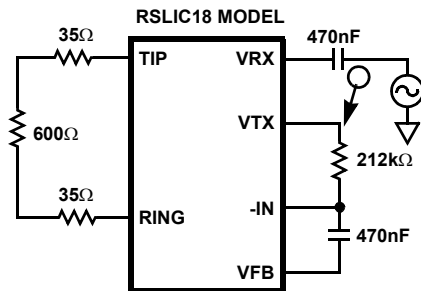


FIGURE 11. G₄₄ RESISTIVE LOAD SIMULATION CIRCUIT

The VRX input of the mode is driven by an AC voltage source. The 4-wire output voltage is measured at the transmit output, VTX, of the device. A dB voltage probe was used to measure the magnitude and a phase voltage probe was used to measure the phase of the frequency response.

EXPECTED RESULTS

The G_{44} results are predicted using the voltage divider relationship shown below.

$$G_{44} = \frac{-Z_O}{Z_L + 2R_P + Z_O} = \frac{-530}{600 + 2(35) + 530} = -0.441 \quad (\text{EQ. 12})$$

The magnitude of the frequency response in the voice band, 300Hz to 3400Hz, should be approximately -7.1dB and the phase should be nearly 180 degrees.

Simulation Example - Complex Load

Most international telephony transmission requirements are defined around a complex 2-wire impedance. The most widely recognized form of the complex network is shown below as well as the device synthesis network to match the impedance.

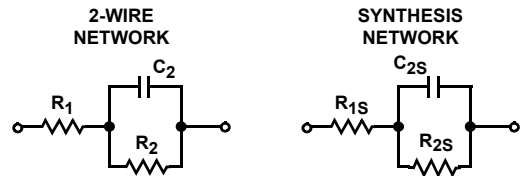


FIGURE 12. TYPICAL COMPLEX IMPEDANCE NETWORK

This simulation example will use the 2-wire complex network for China which is defined as $R_1 = 200\Omega$, $R_2 = 680\Omega$ and $C_2 = 100\text{nF}$.

Device Impedance Synthesis

When matching the device to a complex load the sum of the protection resistance is subtracted from the series resistor R_1 . The other components remain unchanged. The general form of the design equation is shown below.

$$Z_O = Z_L - 2R_P = (R_1 + R_2 \parallel C_2) - 2(R_P) \quad (\text{EQ. 13})$$

Substituting actual component values results in the complex network to be synthesized by the device.

$$Z_O = (200 + 680 \parallel 100\text{n}) - 2(35) = 130 + 680 \parallel 100\text{n} \quad (\text{EQ. 14})$$

Typically the load impedance represents a combination of loop length and phone impedance, therefore a separate term for the loop length (ohms/foot) is not required.

The external resistor, R_{1S} , which programs the synthesized impedance now takes the form of the complex network defined by R_{1S} , R_{2S} and C_{2S} .

$$R_{1S} = 400(R_1 - 2R_P) = 400(130) = 52\text{k}\Omega \quad (\text{EQ. 15})$$

$$R_{2S} = 400(R_2) = 400(680) = 272\text{k}\Omega \quad (\text{EQ. 16})$$

$$C_{2S} = \frac{C_2}{400} = \frac{100\text{n}}{400} = 250\text{pF} \quad (\text{EQ. 17})$$

The resistor value used in the application circuit will be the standard component value nearest to the calculated value.

G₄₂ Simulation

The G_{42} frequency response of the device can be simulated using the circuit of Figure 13.

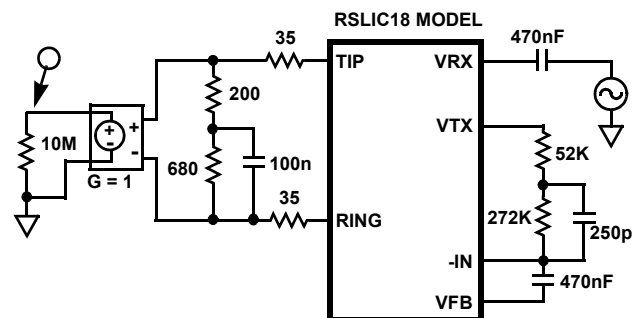


FIGURE 13. G₄₂ COMPLEX LOAD SIMULATION CIRCUIT

EXPECTED RESULTS

Though slightly cumbersome, the voltage divider relationship also applies to the complex matching gain.

$$G_{42} = \frac{-2Z_L}{Z_L + 2R_P + Z_O} \quad (\text{EQ. 18})$$

where: $Z_L = R_1 + R_2 \parallel C_2$
 $R_P = R_P$
 $Z_O = (R_1 + R_2 \parallel C_2) - (2R_P)$

Substituting the above terms into Equation 19, the G_{42} gain equation for complex matching is formed.

$$G_{42} = \frac{-2(R_1 + R_2 \parallel C_2)}{(R_1 + R_2 \parallel C_2) + 2R_P + (R_1 + R_2 \parallel C_2) - 2(R_P)} \quad (\text{EQ. 19})$$

Cancelling the protection resistor terms in the denominator reduces the gain equation into the following simplified form.

$$G_{42} = \frac{-2(R_1 + R_2 \parallel C_2)}{(R_1 + R_2 \parallel C_2) + (R_1 + R_2 \parallel C_2)} = -1 \quad (\text{EQ. 20})$$

Therefore for either resistive or complex matching the G_{42} voltage gain will always be unity and the phase will be nearly 180 degrees.

G₂₄ Simulation

The G_{24} frequency response of the device can be simulated using the circuit of Figure 14.

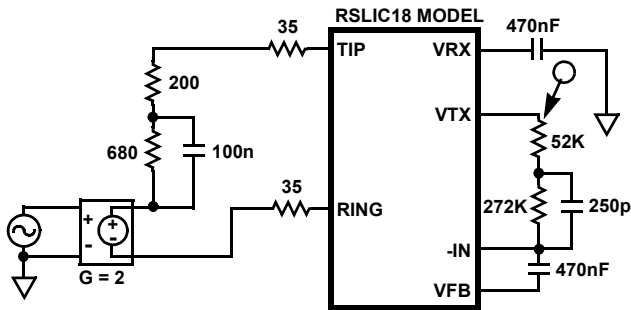


FIGURE 14. G₂₄ COMPLEX LOAD SIMULATION CIRCUIT

EXPECTED RESULTS

The G_{24} results for complex matching are predicted using the voltage divider relationship shown below.

$$G_{24} = \frac{-Z_O}{Z_L + 2R_P + Z_O} \quad (\text{EQ. 21})$$

where: $Z_L = R_1 + R_2 \parallel C_2$
 $R_P = R_P$
 $Z_O = (R_1 + R_2 \parallel C_2) - (2R_P)$

Substituting the above terms into Equation 22, the G_{24} gain equation for complex matching is formed.

$$G_{24} = \frac{-((R_1 + R_2 \parallel C_2) - 2(R_P))}{(R_1 + R_2 \parallel C_2) + 2R_P + ((R_1 + R_2 \parallel C_2) - 2(R_P))} \quad (\text{EQ. 22})$$

Cancelling the protection resistor terms in the denominator and substituting terms reduces the gain equation to the frequency dependent form shown below.

$$G_{42}(\omega) = \frac{-\left[(R_1 - 2R_P) + \frac{R_2}{1 + j\omega C_2 R_2}\right]}{2\left[R_1 + \frac{R_2}{1 + j\omega C_2 R_2}\right]} \quad (\text{EQ. 23})$$

Until now, all relationships have simplified to scalar terms and have not contained frequency dependent components.

Evaluating the gain at 1kHz, results in a voltage gain of 0.459 and a phase of 178 degrees. Simulation results will vary slightly due to device bandwidth.

G₄₄ Simulation

The G_{44} frequency response of the device can be simulated using the circuit of Figure 15.

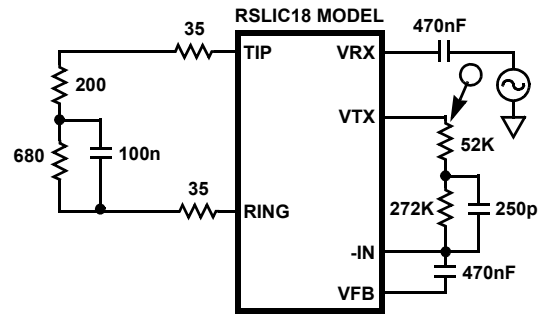


FIGURE 15. G₄₄ COMPLEX LOAD SIMULATION CIRCUIT

EXPECTED RESULTS

The G_{44} results for complex matching are predicted using the voltage divider relationship shown below.

$$G_{44} = \frac{-Z_O}{Z_L + 2R_P + Z_O} \quad (\text{EQ. 24})$$

where: $Z_L = R_1 + R_2 \parallel C_2$
 $R_P = R_P$
 $Z_O = (R_1 + R_2 \parallel C_2) - (2R_P)$

Since the G_{44} gain has the same mathematical expression as the G_{24} gain, the same frequency dependent gain equation applies to both. Evaluating the gain at 1kHz, results in a voltage gain of 0.459 and a phase of 178 degrees. Simulation results will vary slightly due to device bandwidth.

Simulation Results

The following pages contain results for both simulation examples. The magnitude and phase response of each gain path is plotted from 10Hz to 10kHz. The model will accurately predict device frequency response up to 1MHz. In addition to the graphs, numerical data is also provided for reference. Performing the above simulations is suggested when first using the model. The results obtained should agree with those provided herein.

Resistive Matching Simulation Results

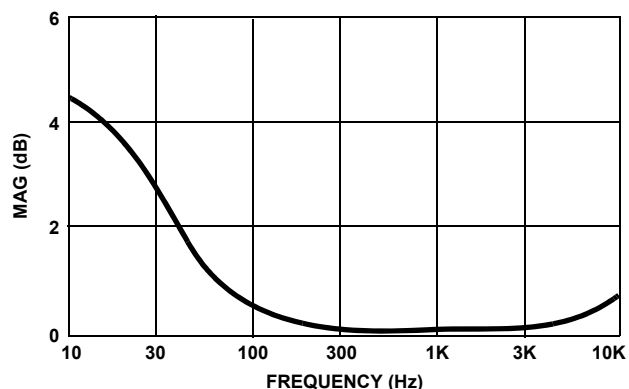


FIGURE 16. G_{42} RESISTIVE MATCHING MAGNITUDE RESPONSE

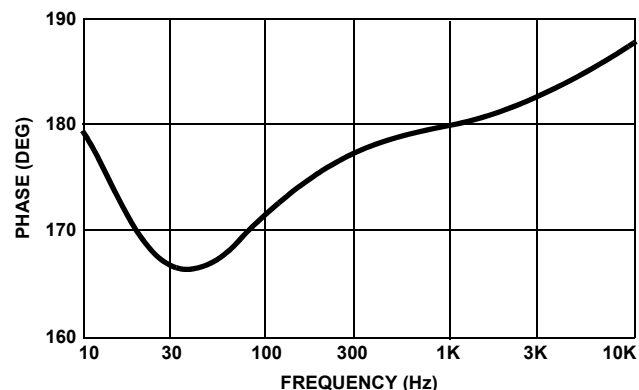


FIGURE 17. G_{42} RESISTIVE MATCHING PHASE RESPONSE

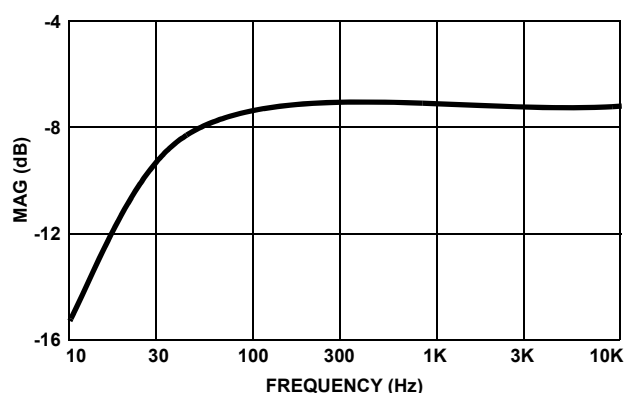


FIGURE 18. G_{24} RESISTIVE MATCHING MAGNITUDE RESPONSE

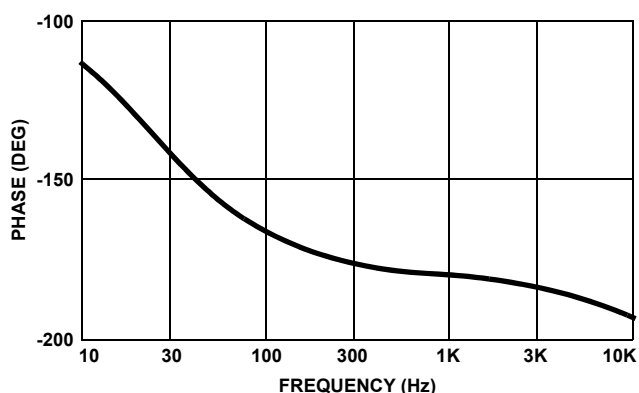


FIGURE 19. G_{24} RESISTIVE MATCHING PHASE RESPONSE

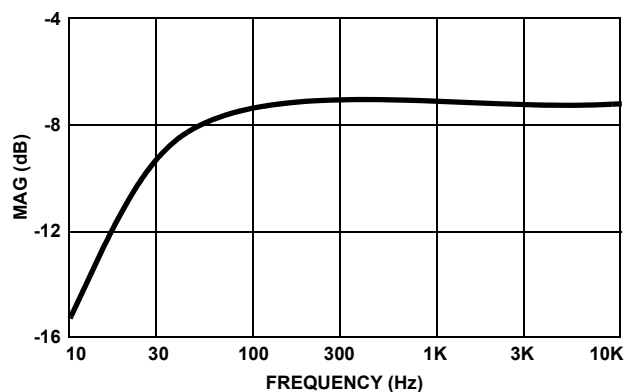


FIGURE 20. G_{44} RESISTIVE MATCHING MAGNITUDE RESPONSE

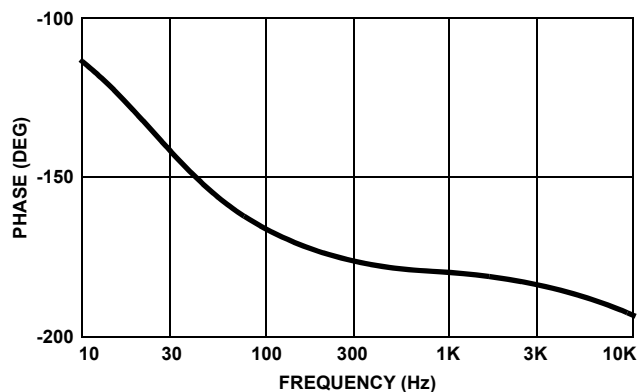


FIGURE 21. G_{44} RESISTIVE MATCHING PHASE RESPONSE

TABLE 1. RESISTIVE MATCHING NUMERICAL RESULTS

FREQUENCY	G_{42}		G_{24}		G_{44}	
	MAGNITUDE (dB)	PHASE (DEG)	MAGNITUDE (dB)	PHASE (DEG)	MAGNITUDE (dB)	PHASE (DEG)
10	4.46	179.9	-15.29	-113.0	-15.29	-113.0
30	2.64	166.8	-9.21	-141.9	-9.21	-141.9
100	0.48	171.5	-7.37	-166.9	-7.37	-166.9
300	0.06	177.1	-7.16	-175.9	-7.16	-175.9
1K	0.02	180.0	-7.14	-180.1	-7.14	-180.1
3K	0.08	182.5	-7.15	-183.8	-7.15	-183.8
10K	0.77	187.7	-7.34	-194.0	-7.34	-194.0

Complex Matching Simulation Results

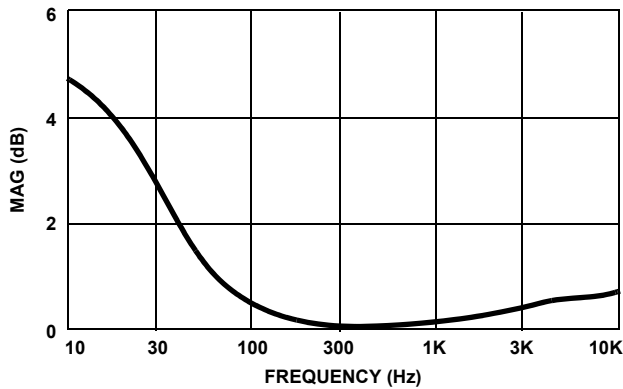


FIGURE 22. G_{42} COMPLEX MATCH MAGNITUDE RESPONSE

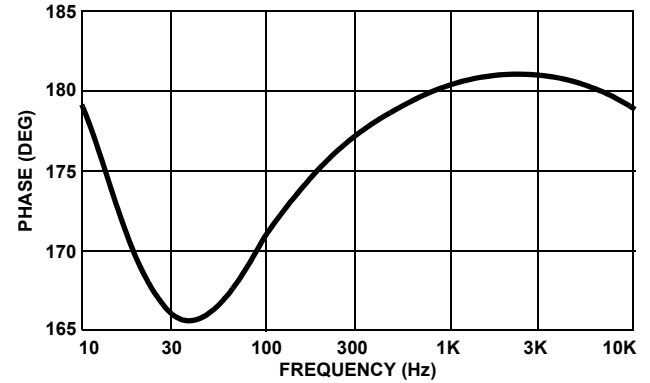


FIGURE 23. G_{42} COMPLEX MATCH PHASE RESPONSE

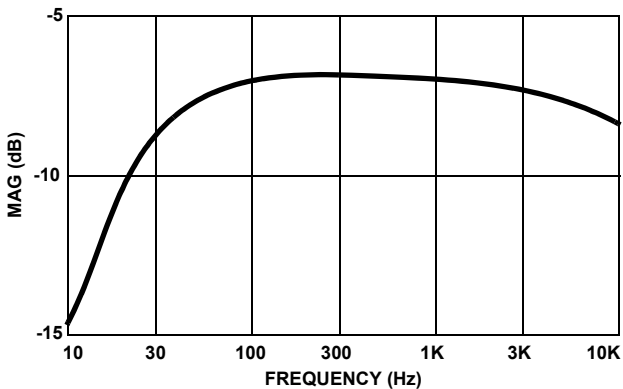


FIGURE 24. G_{24} COMPLEX MATCH MAGNITUDE RESPONSE

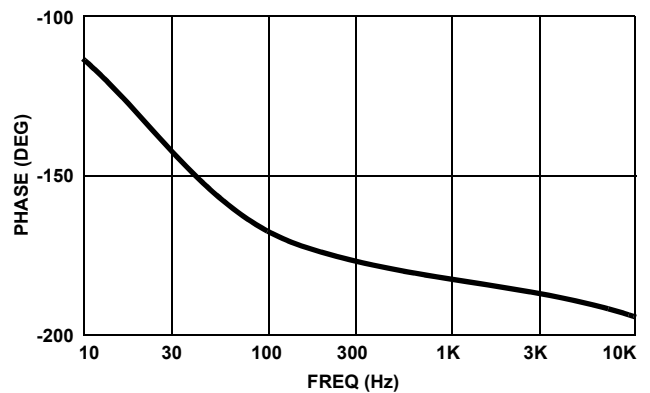


FIGURE 25. G_{24} COMPLEX MATCH PHASE RESPONSE

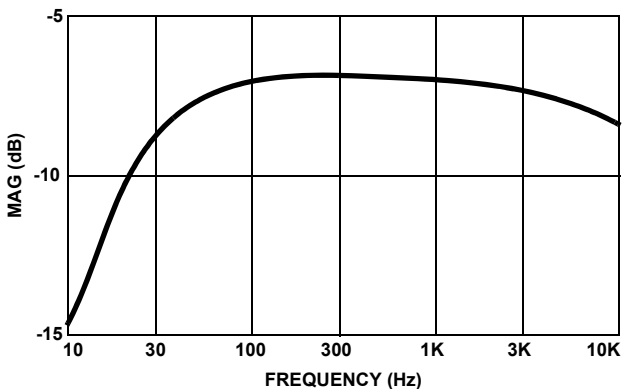


FIGURE 26. G_{44} COMPLEX MATCH MAGNITUDE RESPONSE

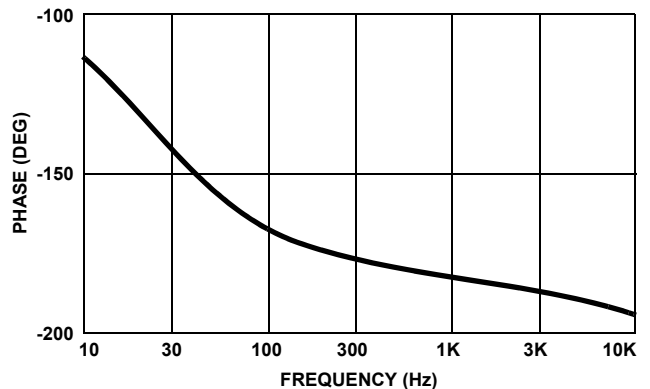


FIGURE 27. G_{44} COMPLEX MATCH PHASE RESPONSE

TABLE 2. COMPLEX MATCH NUMERICAL RESULTS

FREQUENCY	G_{42}		G_{24}		G_{44}	
	MAGNITUDE (dB)	PHASE (DEG)	MAGNITUDE (dB)	PHASE (DEG)	MAGNITUDE (dB)	PHASE (DEG)
10	4.70	179.2	-14.7	-113.8	-14.7	-113.8
30	2.74	165.9	-8.76	-143.0	-8.76	-143.0
100	0.49	171.1	-7.02	-167.6	-7.02	-167.6
300	0.07	177.2	-6.84	-176.8	-6.84	-176.8
1K	0.12	180.4	-6.92	-182.1	-6.92	-182.1
3K	0.42	181.0	-7.34	-187.1	-7.34	-187.1
10K	0.69	178.5	-8.50	-194.0	-8.50	-194.0

SPICE Net List

The following is the complete net list for the macromodel.
Notations have been added to the listing to assist in decoding the net list.

SPICE Net list

Components At Amplifier Block Interconnect Level

```
R_U1_R1      $N_0002 $N_0001 200k
R_U1_R2      $N_0002 $N_0027 200k
R_U1_R3      $N_0035 $N_0043 200k
R_U1_R4      $N_0035 $N_0036 20
R_U1_R5      $N_0003 $N_0044 200k
R_U1_R6      $N_0003 $N_0010 20
R_U1_R7      $N_0036 $N_0029 600k
R_U1_R8      $N_0003 $N_0029 600k
R_U1_R9      $N_0010 $N_0028 600k
R_U1_R10     $N_0035 $N_0028 600k
R_U1_R11     $N_0028 0 150k
R_U1_R12     $N_0029 $N_0034 150k
R_U1_R13     $N_0034 $N_0004 8k
F_U1_F4      $N_0043 $N_0044 VF_U1_F4 -1
VF_U1_F4     $N_0002 $N_0005 0V
R_U1_R23     0 $N_0005 1
V_U1_V1      $N_0014 0 -12V
```

Ring Amplifier Model Components

```
E_U1_HS1_E8  $N_0006 0 $N_0014 $N_0044 59420
E_U1_HS1_E9  $N_0008 0 $N_0007 0 1
E_U1_HS1_E10 $N_0010 0 $N_0009 0 1
R_U1_HS1_R24 $N_0006 $N_0007 13.4G
R_U1_HS1_R25 $N_0011 $N_0009 65k
C_U1_HS1_C2  0 $N_0012 1p
C_U1_HS1_C3  0 $N_0009 1p
R_U1_HS1_R27 $N_0008 $N_0013 65k
C_U1_HS1_C5  0 $N_0013 1p
E_U1_HS1_E12 $N_0011 0 $N_0013 0 1
R_U1_HS1_R29 $N_0012 $N_0007 155k
C_U1_HS1_C6  $N_0010 $N_0044 8p
```

Tip Amplifier Model Components

```
E_U1_HS2_E8  $N_0015 0 $N_0014 $N_0043 49740
E_U1_HS2_E9  $N_0017 0 $N_0016 0 1
E_U1_HS2_E10 $N_0036 0 $N_0018 0 1
R_U1_HS2_R24 $N_0015 $N_0016 11.9G
R_U1_HS2_R25 $N_0019 $N_0018 55k
C_U1_HS2_C2  0 $N_0020 1p
C_U1_HS2_C3  0 $N_0018 1p
R_U1_HS2_R27 $N_0017 $N_0021 56k
```

```
C_U1_HS2_C5  0 $N_0021 1p
E_U1_HS2_E12 $N_0019 0 $N_0021 0 1
R_U1_HS2_R29 $N_0020 $N_0016 132k
C_U1_HS2_C6  $N_0036 $N_0043 5.2p
```

Transmit Amplifier Model Components

```
E_U1_HS3_E8  $N_0023 0 0 $N_0022 4151
E_U1_HS3_E9  $N_0025 0 $N_0024 0 1
E_U1_HS3_E10 $N_0027 0 $N_0026 0 1
R_U1_HS3_R24 $N_0023 $N_0024 1.25G
R_U1_HS3_R25 $N_0025 $N_0026 100k
C_U1_HS3_C2  0 $N_0024 1p
C_U1_HS3_C3  0 $N_0026 1p
```

Sense Amplifier Model Components

```
E_U1_HS4_E8  $N_0030 0 $N_0028 $N_0029 4716
E_U1_HS4_E9  $N_0032 0 $N_0031 0 1
E_U1_HS4_E10 $N_0034 0 $N_0033 0 1
R_U1_HS4_R24 $N_0030 $N_0031 611M
R_U1_HS4_R25 $N_0032 $N_0033 92k
C_U1_HS4_C2  0 $N_0031 1p
C_U1_HS4_C3  0 $N_0033 1p
```

DC Loop Current Model Components

```
G_U1_U4_G1  $N_0037 0 $N_0035 $N_0036 69.4e-6
I_U1_U4_I1  $N_0038 0 DC 34.375e-6
R_U1_U4_R1  $N_0039 0 17k
R_U1_U4_R2  $N_0041 $N_0040 100k
C_U1_U4_C2  0 $N_0039 4.7u
G_U1_U4_G2  $N_0042 0 $N_0036 $N_0035 69.4e-6
R_U1_U4_R6  0 $N_0042 10e6
R_U1_U4_R7  0 $N_0038 10e6
R_U1_U4_R8  0 $N_0037 10e6
D_U1_U4_D6  $N_0042 $N_0038 Dbreak
D_U1_U4_D8  $N_0037 $N_0038 Dbreak
G_U1_U4_G6  $N_0043 $N_0044 $N_0039 0 58.823e-6
G_U1_U4_G8  $N_0039 0 $N_0040 0 4e-3
D_U1_U4_D10 $N_0038 $N_0045 Dbreak
R_U1_U4_R33 0 $N_0045 50k
E_U1_U4_E3  $N_0041 0 $N_0045 0 1
I_U1_U4_I17 $N_0039 0 DC 20u
G_U1_U4_G10 $N_0039 0 $N_0046 0 2.5e-6
V_U1_U4_V16 $N_0046 0 -24
R_U1_U4_R40 0 $N_0040 100e15
V_U1_V1     $N_0014 0 -12V
```

*End of Subcircuit

The files required to load the model in MicroSim Pspice are located on our website at: www.intersil.com.

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
 2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
 3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
 4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.

"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.

"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
 6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
 7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
 9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
 11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)



SALES OFFICES

Renesas Electronics Corporation

<http://www.renesas.com>

Refer to "<http://www.renesas.com/>" for the latest and detailed information.

Renesas Electronics America Inc.
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics Canada Limited
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852-2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338